Number	Hits	Search Text	DB	Time stamp
1	4	(("6160268") or ("6197624")).PN.	USPAT; US-PGPUB;	2004/06/18 08:53
			EPO; JPO; DERWENT;	
2	13	"1174535"	IBM_TDB USPAT;	2004/06/18
			US-PGPUB; EPO; JPO;	08:54
			DERWENT; IBM_TDB	
6	1	"200286423"	USPAT; US-PGPUB;	2004/06/18 08:55
			EPO; JPO; DERWENT;	
7	2	"2000286423"	IBM_TDB USPAT;	2004/06/18
			US-PGPUB; EPO; JPO;	08:56
10	2.5	#0000F04#	DERWENT; IBM_TDB	2004/06/19
10	25	"0088504"	USPAT; US-PGPUB; EPO; JPO;	2004/06/18 09:00
			DERWENT; IBM TDB	
11	0	"20010068784"	USPAT; US-PGPUB;	2004/06/18 08:59
			EPO; JPO; DERWENT;	
12	0	"1020010068784"	IBM_TDB USPAT;	2004/06/18
			US-PGPUB; EPO; JPO;	08:59
			DERWENT; IBM_TDB	0004/06/10
13	0	"10-2001-0068784"	USPAT; US-PGPUB;	2004/06/18 09:00
			EPO; JPO; DERWENT; IBM TDB	
14	3	'KR' and '0088504'	USPAT; US-PGPUB;	2004/06/18 09:00
			EPO; JPO; DERWENT;	
15	139	'bottom gate thin film transistor'	IBM_TDB USPAT;	2004/06/18
			US-PGPUB; EPO; JPO;	09:02
			DERWENT; IBM_TDB	0004/05/10
16	4	'bottom gate thin film transistor' and 'Sanyo'	USPAT; US-PGPUB;	2004/06/18 09:03
			EPO; JPO; DERWENT; IBM TDB	
17	1	JP2000338708	USPAT; US-PGPUB;	2004/06/18 09:04
			EPO; JPO; DERWENT;	
25	897		IBM_TDB USPAT;	2004/06/18
		and 'TFT'	US-PGPUB; EPO; JPO;	09:53
0.7			DERWENT; IBM_TDB	2004/05/10
27	3	<pre>@ad<=20001107 and yamazaki-shunpei.in. and semiconductor-energy-laboratory.as.</pre>	USPAT; US-PGPUB;	2004/06/18 09:44
			EPO; JPO; DERWENT; IBM TDB	

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1		
.3	30	

30	155	@ad<=20001107 and yamazaki-shunpei.in.	USPAT;	2004/06/18
		and 'TFT' and 'bottom gate'	US-PGPUB; EPO; JPO;	09:54
			DERWENT;	
			IBM TDB	
32	701	@ad<=20001107 and 'inverted transistor'	USPAT;	2004/06/18
		<u> </u>	US-PGPUB;	11:01
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	36	<pre>@ad<=20001107 and 'thin film transistor'</pre>	USPAT;	2004/06/18
		and 'selective' near 'doping'	US-PGPUB; EPO; JPO;	08:51
			DERWENT;	
1			IBM TDB	
_	2	<pre>@ad<=20001107 and 'thin film transistor'</pre>	USPĀT;	2002/07/16
		and 'cleaning' near 'native oxide'	US-PGPUB;	14:53
			EPO; JPO;	
			DERWENT;	
	,	0.14.00001107	IBM_TDB	0000 /07 /16
_	1	@ad<=20001107 and 'TFT' and 'cleaning' near 'native oxide'	USPAT;	2002/07/16 14:53
		Hear Hacive Ovide	US-PGPUB; EPO; JPO;	14.00
			DERWENT;	
			IBM TDB	,
-	18	@ad<=20001107 and 'TFT' and 'remove' near	USPAT;	2002/12/17
		'native oxide'	US-PGPUB;	16:10
			EPO; JPO;	
	•	· ·	DERWENT;	
	7	 @ad<=20001107 and 'TFT' and 'removal'	IBM_TDB USPAT;	2002/07/16
-	·	near 'native oxide'	US-PGPUB;	15:06
		Heal Hative Oxide	EPO; JPO;	13.00
			DERWENT;	
			IBM_TDB	
-	590	@ad<=20001107 and "thin film transistor"	USPAT;	2002/07/16
		and "ohmic contact layer"	US-PGPUB;	15:26
			EPO; JPO;	
			DERWENT; IBM TDB	:
_	60	@ad<=20001107 and "thin film transistor"	USPAT;	2002/07/17
		and "remove" near 'oxide'	US-PGPUB;	08:43
			EPO; JPO;	
			DERWENT;	
	_	11205071 CH PV	IBM_TDB	2002/07/16
-	l ₁	"3859716".PN.	USPAT	2002/07/16 17:05
1_	1	"4757026".PN.	USPAT	2002/07/16
		1.07000 12.11		17:05
-	1	"4876213".PN.	USPAT	2002/07/16
				17:05
-	1	"5182620".PN.	USPAT	2002/07/16
		#E266923# PM	IICDAM	17:06
-	1	"5266823".PN.	USPAT	2002/07/16 17:06
_	1	"5323042".PN.	USPAT	2002/07/16
1	*			17:06
-	1	"5998841".PN.	USPAT	2002/07/16
				17:06
-	1	"5962872".PN.	USPAT	2002/07/16
1_	,	"5020721" DM	ווכסאים	17:06
-	1	"5939731".PN.	USPAT	2002/07/16 17:07
_	1	"5804471".PN.	USPAT	2002/07/16
				17:07
-	1	"5856689".PN.	USPAT	2002/07/16
				17:08
	1	"5804471".PN.	USPAT	2002/07/16
				17:08

_	3055	((438/149) or (438/158) or (438/315) or (438/334)).CCLS.	USPAT; US-PGPUB; EPO; JPO;	2003/07/08 07:41
			DERWENT;	
_	6	(((438/149) or (438/158) or (438/315) or	IBM_TDB USPAT;	2003/07/07
		(438/334)).CCLS.) and @ad<=20001107 and	US-PGPUB;	13:51
		"thin film transistor" and "remove" near 'oxide'	EPO; JPO; DERWENT;	
		Oxide	IBM_TDB	
-	608	(((438/149) or (438/158) or (438/315) or (438/334)).CCLS.) and @ad<=20001107 and	USPAT;	2002/07/17
		"thin film transistor"	US-PGPUB; EPO; JPO;	00:46
			DERWENT;	
_	5525	((438/149) or (438/158-159) or (438/315)	IBM_TDB USPAT;	2002/12/17
		or (438/334) or (438/163) or (438/166) or	US-PGPUB;	15:43
		(257/69) or (257/72) or (257/59)).CCLS.	EPO; JPO; DERWENT;	
			IBM_TDB	
-	16	(((438/149) or (438/158-159) or (438/315) or (438/334) or (438/163) or (438/166) or	USPAT; US-PGPUB;	2003/07/08
		(257/69) or (257/72) or (257/59)).CCLS.)	EPO; JPO;	
		and @ad<=20001107 and "thin film transistor" and "remove" near 'oxide'	DERWENT; IBM TDB	
-	1	@ad<=20001107 and 'thin film transistor'	USPAT;	2002/12/17
	İ	and 'burried gate'	US-PGPUB; EPO; JPO;	15:56
			DERWENT;	
	20420	0-14 20001107 1 155- 5-1- 5-1- 5-1-	IBM_TDB	2002/12/17
-	30430	@ad<=20001107 and 'thin film transistor'	USPAT; US-PGPUB;	2002/12/17 15:59
			EPO; JPO;	
			DERWENT; IBM_TDB	
-	779	(@ad<=20001107 and 'thin film transistor'	USPAT;	2002/12/17
) and short same channel	US-PGPUB; EPO; JPO;	16:01
			DERWENT;	
_	719	 (@ad<=20001107 and 'thin film transistor'	IBM_TDB USPAT;	2002/12/17
) and short same channel and gate	US-PGPUB;	16:02
			EPO; JPO; DERWENT;	
			IBM_TDB	
_	18	<pre>@ad<=20001107 and 'TFT' and 'remove' near 'native oxide'</pre>	USPAT; US-PGPUB;	2002/12/18
		native oxide	EPO; JPO;	00.30
			DERWENT; IBM TDB	
_	1	"5641974".PN.	USPAT	2002/12/17
_	1	"5780871".PN.	USPAT	16:13 2002/12/17
				16:13
-	1	"5837619".PN.	USPAT	2002/12/17 16:14
-	1	"5882165".PN.	USPAT	2002/12/17
_	1	"5917571".PN.	USPAT	16:14 2002/12/17
_	1	"6177302".PN.	USPAT	16:14 2002/12/17
_	4767	((257/59) or (257/61) or (257/72) or	USPAT;	16:14 2003/07/08
-	1 4/6/	((257/347) or (257/61) or (257/72) or (257/347) or (349/42-43)).CCLS.	US-PGPUB;	07:41
			EPO; JPO;	:
			DERWENT; IBM_TDB	
-	114	@ad<=20001107 and 'bottom gate TFT'	USPĀT;	2003/07/08
			US-PGPUB; EPO; JPO;	07:45
			DERWENT;	
1	1	I	IBM TDB	1

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	1 -	L (UC107C41U) DV	ticham.	1 2002 (07 /07
-	2	("6107641").PN.	USPAT;	2003/07/07
			US-PGPUB;	14:05
			EPO; JPO;	<u> </u>
			DERWENT;	
			IBM_TDB	1
-	3424	((438/149) or (438/158) or (438/315) or	USPAT;	2003/07/08
		(438/334)).CCLS.	US-PGPUB;	07:42
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	5311	((257/59) or (257/61) or (257/72) or	USPAT;	2003/07/08
		(257/347) or (349/42-43)).CCLS.	US-PGPUB;	07:44
1		(30,7,01.7, 02 (0.3, 12 13,7,10023)	EPO; JPO;	
:			DERWENT;	
			IBM TDB	
1	16	(((438/149) or (438/158-159) or (438/315)	USPAT;	2003/07/08
-	10	_ , , , , = , , , , , , , , , , , , , ,	US-PGPUB;	07:44
		or (438/334) or (438/163) or (438/166) or		07:44
		(257/69) or (257/72) or (257/59)).CCLS.)	EPO; JPO;	
		and @ad<=20001107 and 'thin film	DERWENT;	
1		transistor' and 'remove' near 'oxide'	IBM_TDB	
-	493		USPAT;	2004/06/18
		'TFT'	US-PGPUB;	09:02
İ			EPO; JPO;	
			DERWENT;	
1			IBM_TDB	
-	2	"20020090774"	USPAT;	2004/06/10
			US-PGPUB;	14:41
			EPO; JPO;	
		•	DERWENT;	
			IBM TDB	
_	1	"5712191".PN.	USPAT	2004/06/10
	1			14:59
_	545	@ad<=20001107 and 'bottom gate' with	USPAT;	2004/06/18
		'TFT'	US-PGPUB;	10:56
			EPO; JPO;	
			DERWENT;	<u> </u>
			IBM TDB	
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